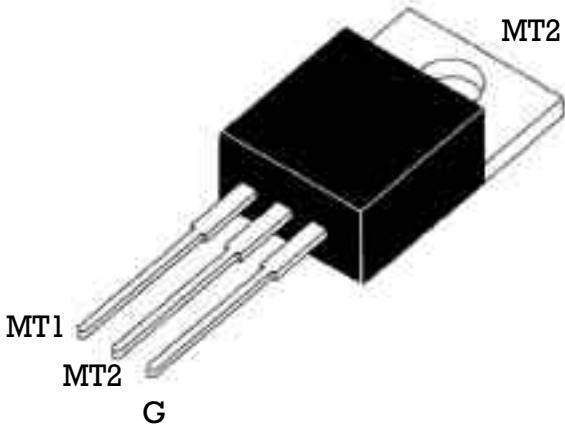


HIGH COMMUTATION TRIAC

TO220-AB  MT1 MT2 G	On-State Current 8 Amp Gate Trigger Current $\leq 25 \text{ mA}$ to $\leq 50 \text{ mA}$ Off-State Voltage $200 \text{ V} \div 600 \text{ V}$ This series of TRIACs uses a high performance PNP technology. These parts are intended for general purpose AC switching applications with highly inductive loads.
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Absolute Maximum Ratings, according to IEC publication No. 134

SYMBOL	PARAMETER	CONDITIONS	Min.	Max.	Unit
$I_{T(RMS)}$	RMS On-state Current	All Conduction Angle, $T_C = 110^\circ\text{C}$	8		A
I_{TSM}	Non-repetitive On-State Current	Full Cycle, 60 Hz	84		A
I_{TSM}	Non-repetitive On-State Current	Full Cycle, 50 Hz	80		A
I^2t	Fusing Current	$t_p = 10 \text{ ms}$, Half Cycle	36		A ² s
I_{GM}	Peak Gate Current	$20 \mu\text{s max.}$ $T_j = 125^\circ\text{C}$		4	A
$P_{G(AV)}$	Average Gate Power Dissipation	$T_j = 125^\circ\text{C}$		1	W
di/dt	Critical rate of rise of on-state current	$I_G = 2 \times I_{GT}$, $t_r \leq 100\text{ns}$ $f = 120 \text{ Hz}$, $T_j = 125^\circ\text{C}$	50		A/ μs
T_j	Operating Temperature		-40	+125	$^\circ\text{C}$
T_{stg}	Storage Temperature		-40	+150	$^\circ\text{C}$

SYMBOL	PARAMETER	VOLTAGE			Unit
		B	D	M	
V_{DRM} V_{RRM}	Repetitive Peak Off State Voltage	200	400	600	V

HIGH COMMUTATION TRIAC

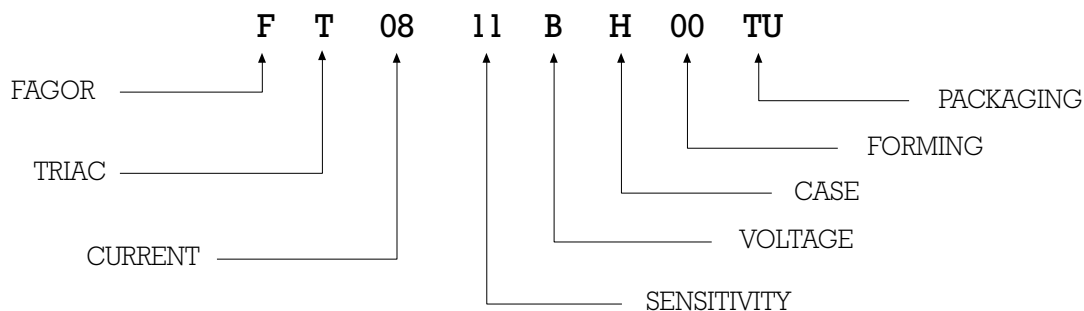
Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	Quadrant		SENSITIVITY			Unit
					11	14	16	
$I_{GT}^{(1)}$	Gate Trigger Current	$V_D = 12 V_{DC}$, $R_L = 30\Omega$ $T_j = 25^\circ C$	Q1÷Q3	MAX	25	35	50	mA mA
I_{DRM}/I_{RRM}	Off-State Leakage Current	$V_R = V_{RRM}$, $T_j = 125^\circ C$ $T_j = 25^\circ C$		MAX MAX	1 5			mA μA
$V_{to}^{(2)}$	Threshold Voltage	$T_j = 125^\circ C$		MAX	0.85			V
$R_d^{(2)}$	Dynamic Resistance	$T_j = 125^\circ C$		MAX	60			m Ω
$V_{TM}^{(2)}$	On-state Voltage	$I_T = 11 \text{ Amp}$, $t_p = 380 \mu s$, $T_j = 25^\circ C$		MAX	1.55			V
V_{GT}	Gate Trigger Voltage	$V_D = 12 V_{DC}$, $R_L = 30\Omega$, $T_j = 25^\circ C$	Q1÷Q3	MAX	1.3			V
V_{GD}	Gate Non Trigger Voltage	$V_D = V_{DRM}$, $R_L = 3.3K\Omega$, $T_j = 125^\circ C$	Q1÷Q3	MIN	0.2			V
$I_H^{(2)}$	Holding Current	$I_T = 100 \text{ mA}$, Gate open, $T_j = 25^\circ C$		MAX	25	35	50	mA
I_L	Latching Current	$I_G = 1.2 I_{GT}$, $T_j = 25^\circ C$	Q1,Q3 Q2	MAX MAX	40 50	50 60	70 80	mA
$dv/dt^{(2)}$	Critical Rate of Voltage Rise	$V_D = 0.67 \times V_{DRM}$, Gate open $T_j = 125^\circ C$		MIN	200	400	1000	V/ μs
$(dI/dt)c^{(2)}$	Critical Rate of Current Rise	$(dv/dt)c = 0.1 \text{ V}/\mu s$, $T_j = 125^\circ C$ $(dv/dt)c = 10 \text{ V}/\mu s$, $T_j = 125^\circ C$ without snubber, $T_j = 125^\circ C$		MIN MIN MIN	- - 4	- - 4.5	- - 7	A/ms
$R_{th(j-c)}$	Thermal Resistance Junction-Case				1.6			$^\circ C/W$
$R_{th(j-a)}$	Thermal Resistance Junction-Ambient				60			$^\circ C/W$

(1) Minimum I_{GT} is guaranteed at 5% of I_{GT} max.

(2) For either polarity of electrode MT2 voltage with reference to electrode MT1.

PART NUMBER INFORMATION



HIGH COMMUTATION TRIAC

Fig. 1: Maximum power dissipation versus RMS on-state current (full cycle).

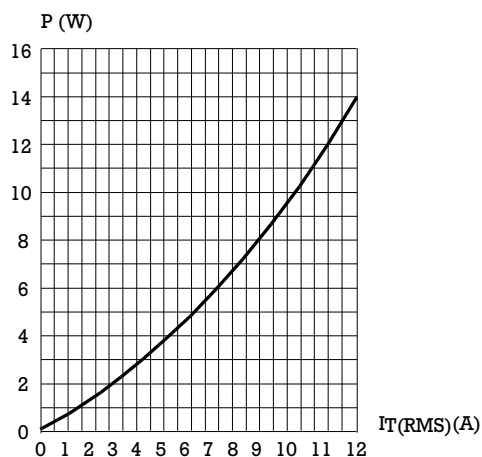


Fig. 3: : Relative variation of thermal impedance versus pulse duration.

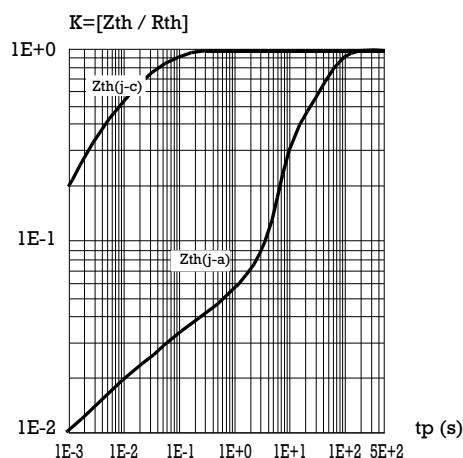


Fig. 5: Surge peak on-state current versus number of cycles

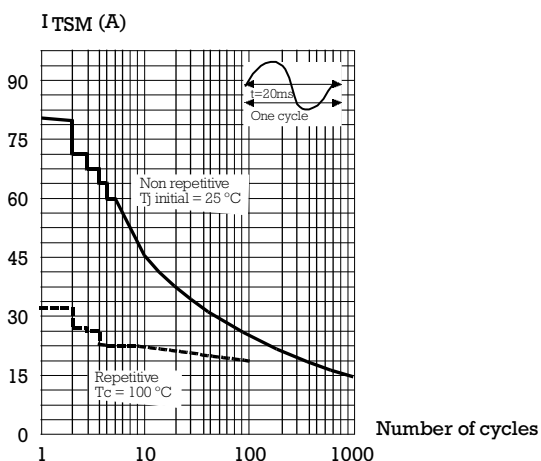


Fig. 2: RMS on-state current versus case temperature (full cycle).

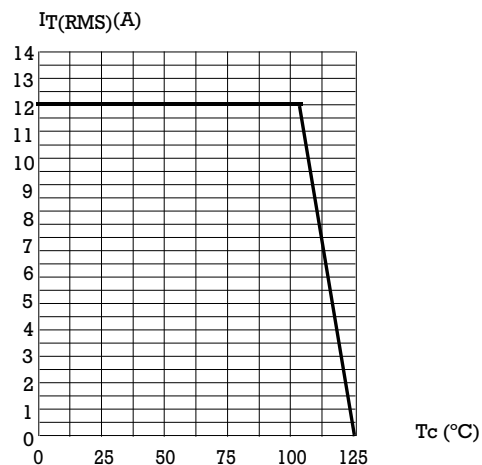


Fig. 4: On-state characteristics (maximum values)

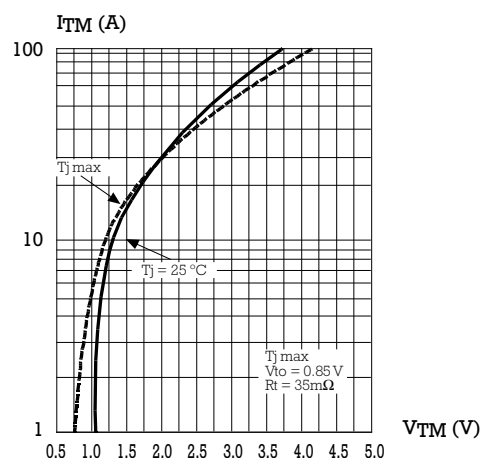
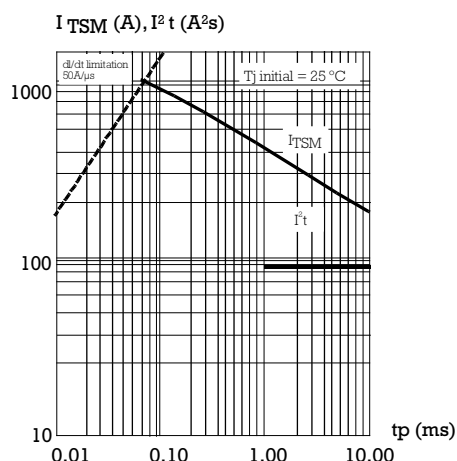


Fig. 6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$, and corresponding value of $I^2 t$.



HIGH COMMUTATION TRIAC

Fig. 7: Relative variation of gate trigger current, holding current and latching versus junction temperature (typical values)

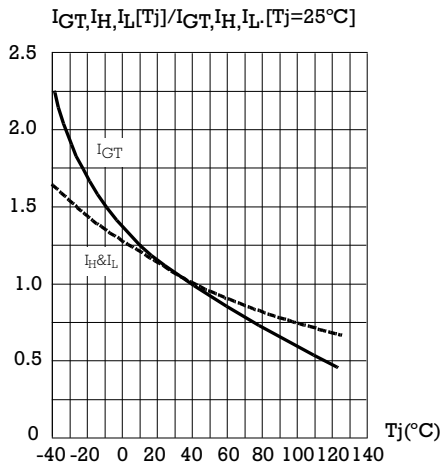
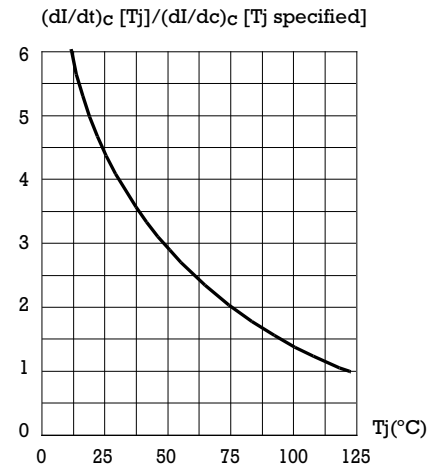


Fig. 8: Relative variation of critical rate of decrease of main current versus junction temperature



PACKAGE MECHANICAL DATA TO-220AB (Plastic)

